

Silicon NPN Power Transistors

BU1506DX

DESCRIPTION

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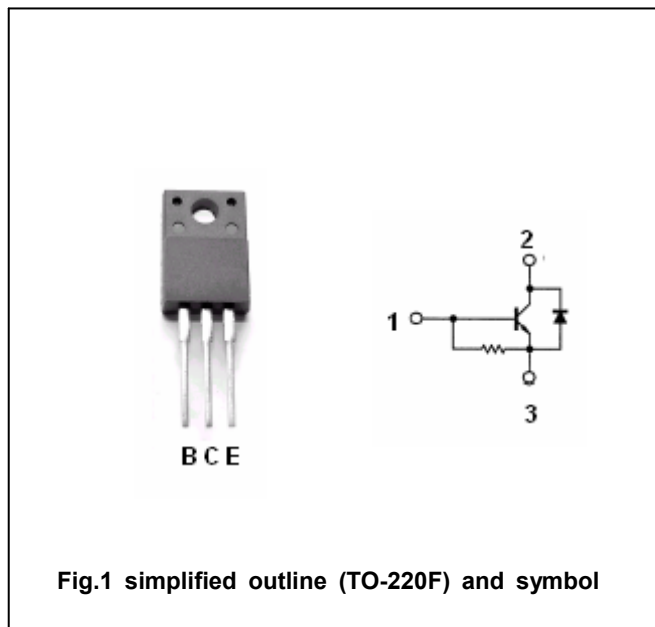
- With TO-220F package
- High voltage
- High speed switching
- Built-in damper diode.

APPLICATIONS

- For use in horizontal deflection circuits of colour TV receivers.

PINNING

PIN	DESCRIPTION
1	Base
2	Collector
3	Emitter



Absolute maximum ratings (Ta=25°C)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V <sub>CBO</sub>	Collector-base voltage	Open emitter	1500	V
V <sub>CEO</sub>	Collector-emitter voltage	Open base	700	V
V <sub>EBO</sub>	Emitter-base voltage	Open collector	7.5	V
I <sub>C</sub>	Collector current		5	A
I <sub>CM</sub>	Collector current-peak		8	A
I <sub>B</sub>	Base current		3	A
I <sub>BM</sub>	Base current-peak		8	A
P <sub>C</sub>	Collector dissipation	T <sub>C</sub> =25°C	32	W
T <sub>j</sub>	Junction temperature		150	°C
T <sub>stg</sub>	Storage temperature		-40~150	°C

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## CHARACTERISTICS

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 $T_j=25^\circ\text{C}$  unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)EBO}$	Emitter-base breakdown voltage	$I_E=600\text{mA}; I_C=0$	7.5	13.5		V
$V_{CEO(SUS)}$	Collector-emitter sustaining voltage	$I_C=100\text{mA}; I_B=0; L=25\text{mH}$	700			V
$V_{CEsat}$	Collector-emitter saturation voltage	$I_C=3\text{A}; I_B=0.79\text{A}$			5.0	V
$V_{BEsat}$	Base-emitter saturation voltage	$I_C=3\text{A}; I_B=0.79\text{A}$			1.1	V
$I_{CES}$	Collector cut-off current	$V_{CE}=\text{rated}; V_{BE}=0$ $T_j=125^\circ\text{C}$			1.0 2.0	mA
$I_{EBO}$	Emitter cut-off current	$V_{EB}=7.5\text{V}; I_C=0$	90		180	mA
$h_{FE-1}$	DC current gain	$I_C=0.3\text{A}; V_{CE}=5\text{V}$		12		
$h_{FE-2}$	DC current gain	$I_C=3.0\text{A}; V_{CE}=5\text{V}$	3.8	5.5	7.5	
$V_F$	Diode forward voltage	$I_F=3.0\text{A}$		1.6	2.0	V
$C_C$	Collector output capacitance	$I_E=0, f=1\text{MHz}; V_{CB}=10\text{V}$		47		pF

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PACKAGE OUTLINE

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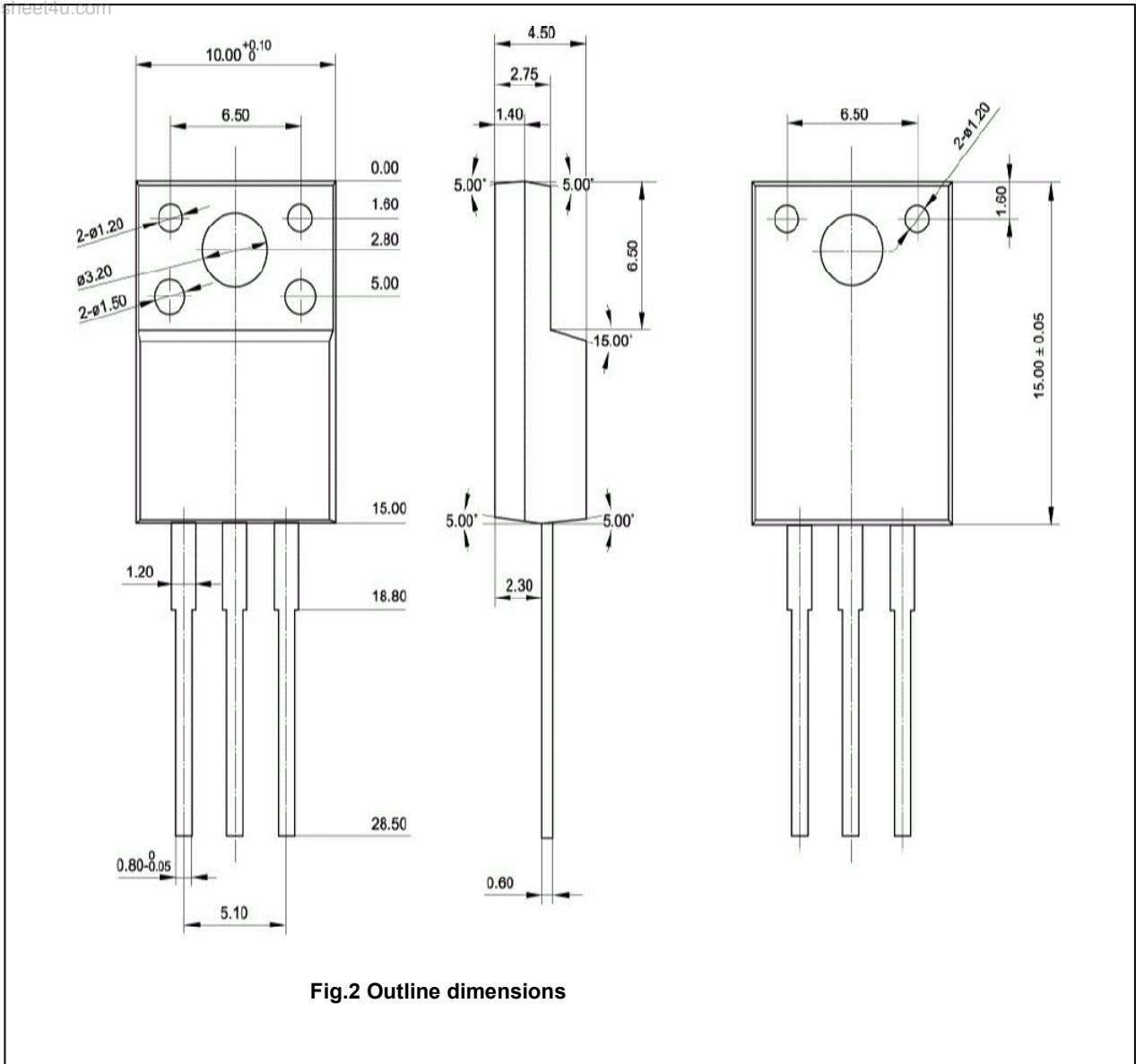


Fig.2 Outline dimensions